

# 1A CMOS Linear Regulator

## General Description

The EMP8995 low-dropout (LDO) CMOS linear regulators feature low dropout voltage (510mV@1A), low quiescent current (120µA), and fast transient response. It guarantees delivery of 1A output current and supports preset 3.3V output voltages.

The regulator is stable with small ceramic capacitive loads (2.2µF typical). The EMP8995 is available in miniature SOT-223 packages.

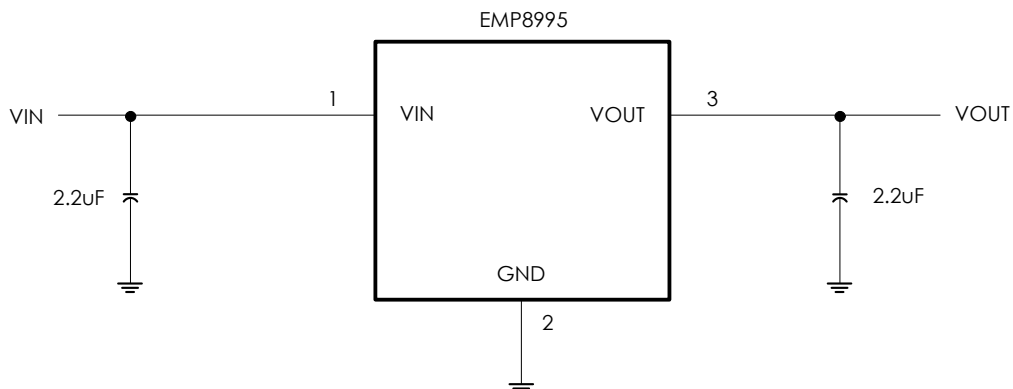
## Applications

- SMPS Post Regulator
- DSP, FPGA and Microprocessor Power
- Wireless Devices
- PC Peripherals
- LCD TV / Monitors
- Portable handheld Devices

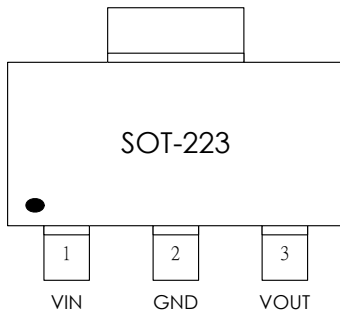
## Features

- 1A guaranteed output current
- 53dB PSRR @1kHz,  $V_{out}=3.3V$ ,  $V_{in}=4.3V$ ,  $I_{load}=1A$
- 30µV RMS output voltage noise @10mA
- 510mV typical dropout at 1A
- 120µA typical quiescent current
- Less than 1nA (typical) @ shutdown mode
- Fast line and load transient response
- Stable with small ceramic output capacitors
- Over temperature and over current protection
- ±2% output voltage tolerance

## Typical Application



## Connection Diagram SOT-223 (TOP View)



## Order Information

EMP8995-XXVE03NRR

XX    Output voltage

VE03    SOT-223 Package

NRR    RoHS & Halogen free package

Rating: -40 to 85°C

Package in Tape & Reel

## Order, Mark & Packing Information

Package	Vout	Product ID.	Marking	Packing
SOT-223	3.3V	EMP8995-XXVE03NRR	<p>8995 Tracking Code</p> <p>PIN1 DOT</p> <p>1 VIN    2 GND    3 VOUT</p>	Tape & Reel 3kpcs

## Pin Functions

Name	SOT-223	Function
VIN	1	<b>Supply Voltage Input.</b> Require a minimum input capacitor of close to 2.2μF to ensure stability and sufficient decoupling from the ground pin.
GND	2	Ground Pin.
VOUT	3	Output Voltage Feedback.

## Absolute Maximum Ratings (Notes 1, 2)

V <sub>IN</sub> , V <sub>OUT</sub>	-0.3V to 6.0V	Lead Temperature (Soldering, 10 sec.)	260°C
Power Dissipation	(Note 3)	ESD Rating	
Storage Temperature Range	-65°C to 150°C	HBM	2kV
Junction Temperature (T <sub>J</sub> )	150°C	MM	200V

## Operating Ratings (Note 1), (Note 2)

Temperature Range	-40°C to 85°C	Thermal Resistance (θ <sub>JA</sub> ) (Note 3)	
Supply Voltage	V <sub>out</sub> +1V to 5.5V	SOT-223	115°C/W

## Electrical Characteristics

Unless otherwise specified, all limits guaranteed for V<sub>IN</sub> = V<sub>OUT</sub> + 1V, C<sub>IN</sub> = C<sub>OUT</sub> = 2.2µF, T<sub>a</sub> = 25°C.

**Boldface** limits apply for the operating temperature extremes: -40°C and 85°C.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V <sub>IN</sub>	Input Voltage		<b>4.0</b>		<b>5.5</b>	V
ΔV <sub>OTL</sub>	Output Voltage Tolerance	100µA ≤ I <sub>OUT</sub> ≤ 1000mA V <sub>OUT(NOM)</sub> + 1V ≤ V <sub>IN</sub> ≤ 5.5V	-2 <b>-3</b>		+2 <b>+3</b>	% of V <sub>OUT(NOM)</sub>
I <sub>OUT</sub>	Maximum Output Current	Average DC Current Rating	1000			mA
I <sub>LIMIT</sub>	Output Current Limit		1000	1300		mA
I <sub>Q</sub>	Supply Current	I <sub>OUT</sub> = 0mA I <sub>OUT</sub> = 1000mA		120 350		µA
V <sub>DO</sub>	Dropout Voltage	I <sub>OUT</sub> = 50mA I <sub>OUT</sub> = 300mA I <sub>OUT</sub> = 600mA I <sub>OUT</sub> = 1000mA		22 130 270 510		mV
ΔV <sub>OUT</sub>	Line Regulation	I <sub>OUT</sub> = 1mA, (V <sub>OUT</sub> + 1V) ≤ V <sub>IN</sub> ≤ 5.5V	-0.15	0.1	0.15	%/V
	Load Regulation	1mA ≤ I <sub>OUT</sub> ≤ 1000mA		0.001		%/mA
e <sub>n</sub>	Output Voltage Noise	I <sub>OUT</sub> = 10mA, 10Hz ≤ f ≤ 100kHz		130		µV <sub>RMS</sub>
T <sub>SD</sub>	Thermal Shutdown Temperature			165		°C
	Thermal Shutdown Hysteresis			30		

**Note 1:** Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

**Note 2:** All voltages are with respect to the potential at the ground pin.

**Note 3:** Maximum Power dissipation for the device is calculated using the following equations:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

where T<sub>J(MAX)</sub> is the maximum junction temperature, T<sub>A</sub> is the ambient temperature, and θ<sub>JA</sub> is the junction-to-ambient thermal resistance.

Functional Block Diagram

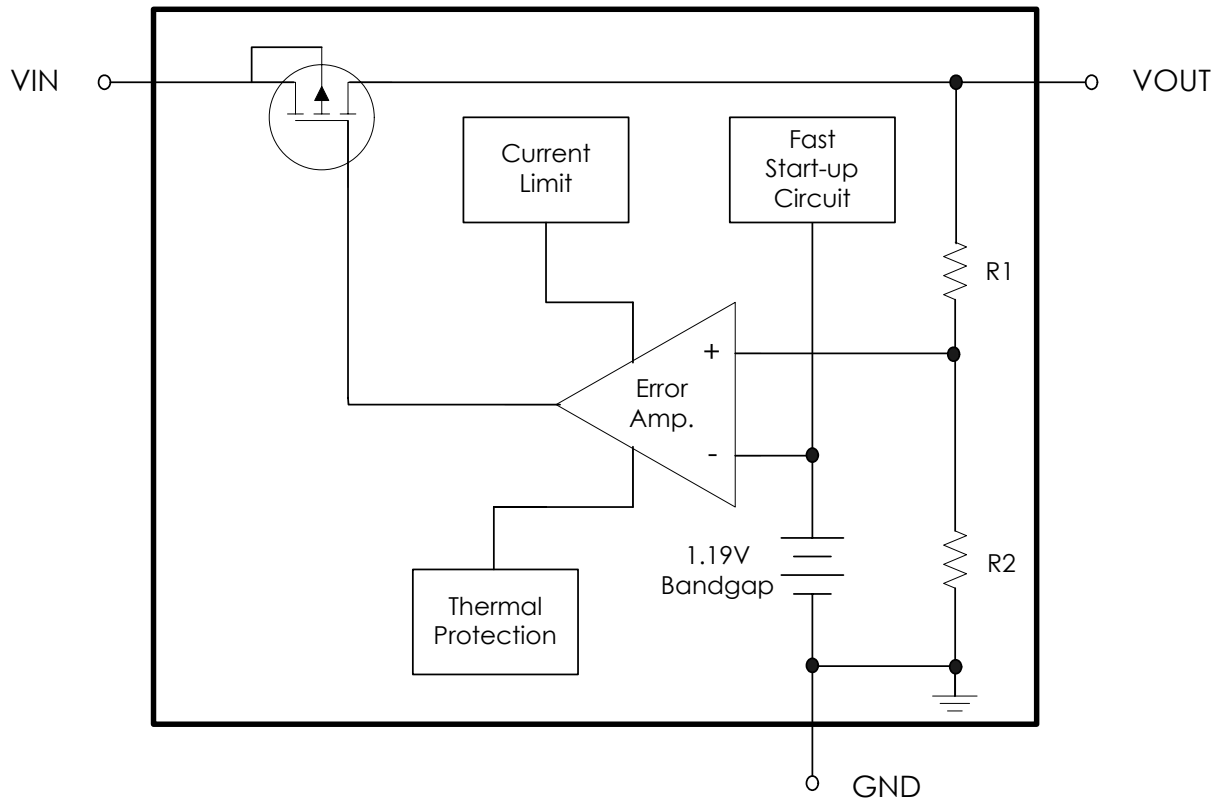
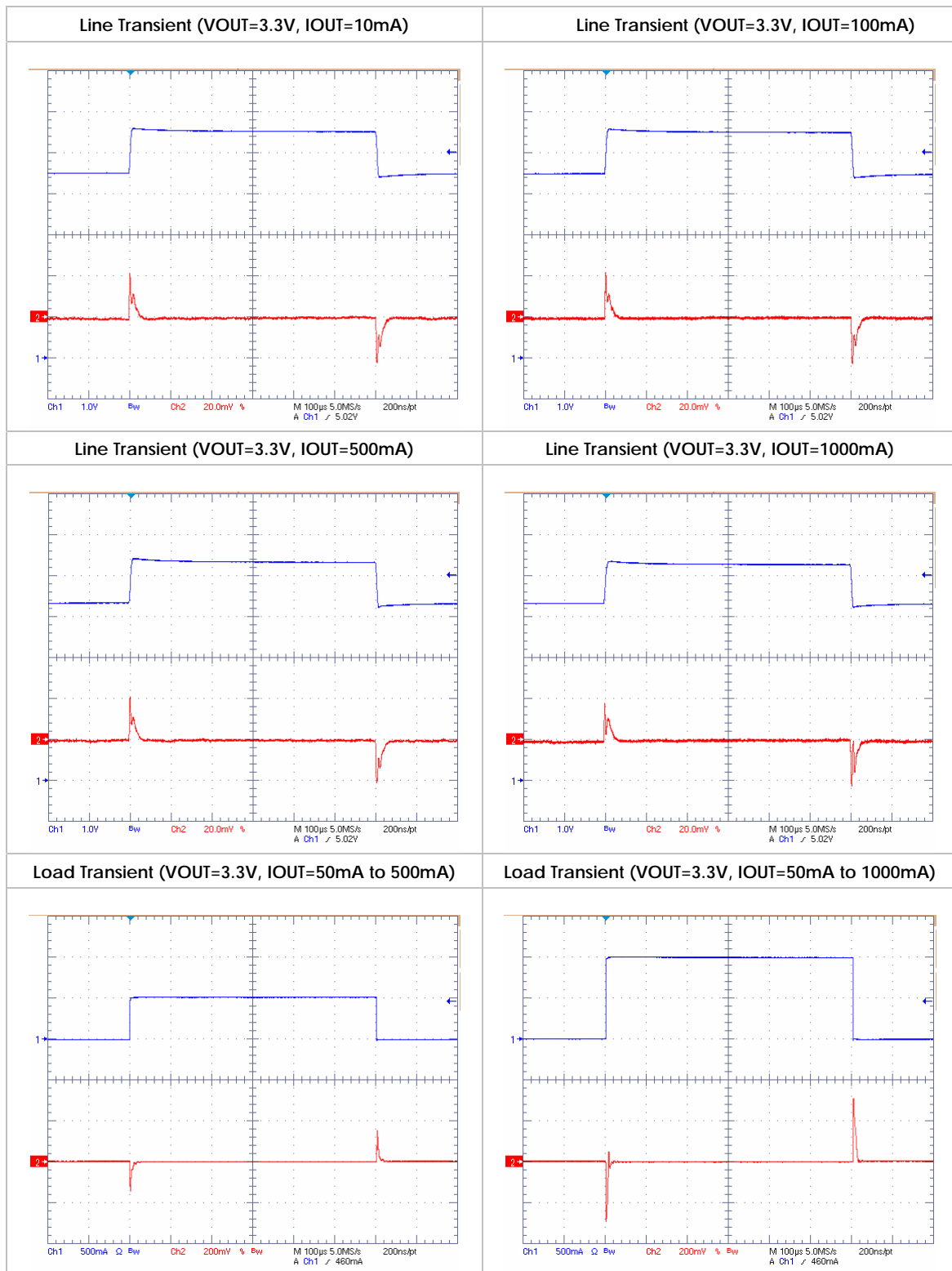


Fig.1 Functional Block Diagram of EMP8995

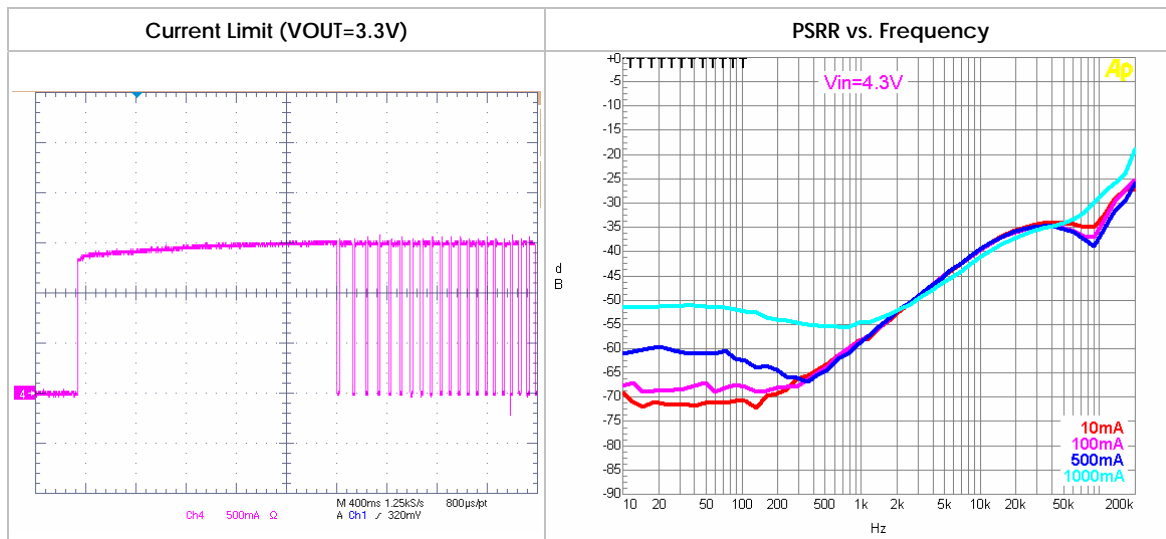
## Typical Performance Characteristics

Unless otherwise specified,  $V_{IN} = V_{OUT(NOM)} + 1V$ ,  $C_{IN} = C_{OUT} = 2.2\mu F$ ,  $T_A = 25^\circ C$ .



## Typical Performance Characteristics (cont.)

Unless otherwise specified,  $V_{IN} = V_{OUT(NOM)} + 1V$ ,  $C_{IN} = C_{OUT} = 2.2\mu F$ ,  $T_A = 25^\circ C$ .



## Application Information

### General Description

Referring to Fig.1 as shown in the Functional Block Diagram section, the EMP8995 adopts the classical regulator topology in which negative feedback control is used to perform the desired voltage regulating function. The negative feedback is formed by using feedback resistors (R1, R2) to sample the output voltage for the non-inverting input of the error amplifier, whose inverting input is set to the bandgap reference voltage. By virtue of its high open-loop gain, the error amplifier operates to ensure that the sampled output feedback voltage at its non-inverting input is virtually equal to the preset bandgap reference voltage.

The error amplifier compares the voltage difference at its inputs and produces an appropriate driving voltage to the P-channel MOS pass transistor to control the amount of current reaching the output. If there are changes in the output voltage due to load changes, the feedback resistors register such changes to the non-inverting input of the error amplifier. The error amplifier then adjusts its driving voltage to maintain virtual short between its two input nodes under all loading conditions. In a nutshell, the regulation of the output voltage is achieved as a direct result of the error amplifier keeping its input voltages equal. This negative feedback control topology is further augmented by the shutdown, the fault detection, and the temperature and current protection circuitry.

### Output Capacitor

The EMP8995 is specially designed for use with ceramic output capacitors of as low as 2.2 $\mu$ F to take advantage of the savings in cost and space as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) be restricted to less than 0.5 $\Omega$ . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as for situations where the application systems are not physically located immediately adjacent to the battery power source. Typical ceramic capacitors suitable for use with the EMP8995 are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within  $\pm 20\%$  and  $\pm 10\%$ , respectively, as the temperature increases.

### No-Load Stability

The EMP8995 is capable of stable operation during no-load conditions, a mandatory feature for some applications such as CMOS RAM keep-alive operations.

### Input Capacitor

A minimum input capacitance of 2.2 $\mu$ F is required for EMP8995. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10 $\mu$ F tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.

### Power Dissipation and Thermal Shutdown

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The EMP8995 relies on dedicated thermal shutdown circuitry to limit its total power dissipation. An IC junction temperature  $T_J$  exceeding 165 $^{\circ}$ C will trigger the thermal shutdown logic, turning off the P-channel MOS pass transistor. The pass transistor turns on again after the junction cools off by about 30 $^{\circ}$ C. When continuous thermal overload conditions persist, this thermal shutdown action then results in a pulsed waveform at the output of the regulator. The concept of thermal resistance  $\theta_{JA}$  ( $^{\circ}$ C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between  $\theta_{JA}$  and  $T_J$  is as follows:

$$T_J = \theta_{JA} (P_D) + T_A$$

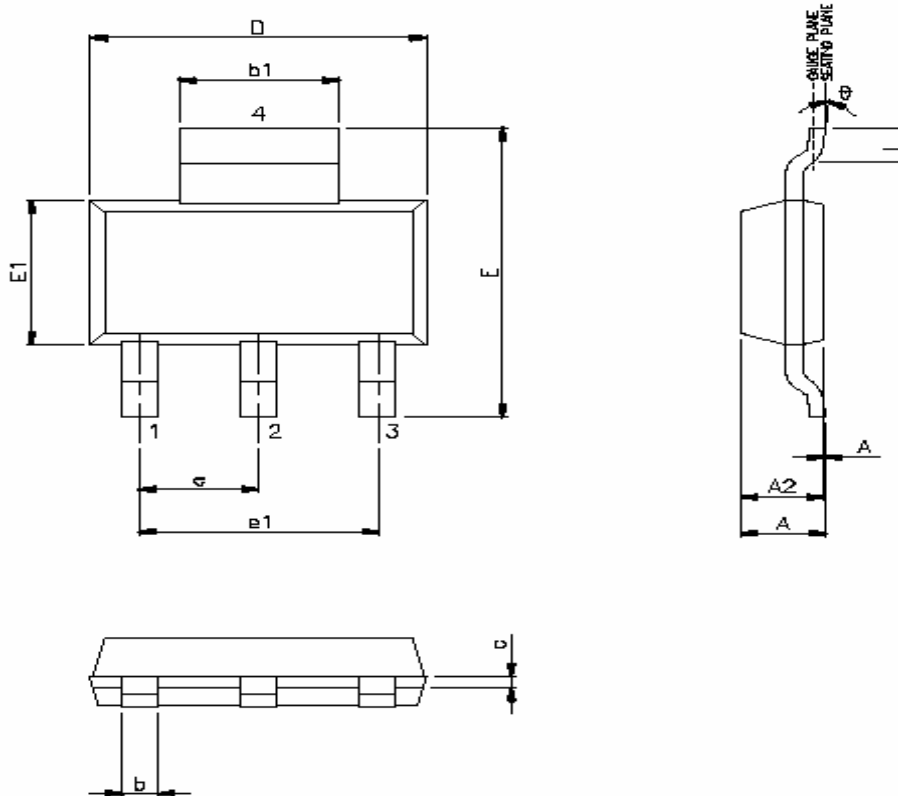
$T_A$  is the ambient temperature, and  $P_D$  is the power generated by the IC and can be written as:

$$P_D = I_{OUT} (V_{IN} - V_{OUT})$$

As the above equations show, it is desirable to work with ICs whose  $\theta_{JA}$  values are small such that  $T_J$  does not increase strongly with  $P_D$ . To avoid thermally overloading the EMP8995, refrain from exceeding the absolute maximum junction temperature rating of 150°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly.



Package Outline drawing  
SOT-223



SYMBPLS	MIN.	NOM.	MAX.
A	—	—	1.80
A1	0.02		0.10
A2	1.50	1.60	1.70
b	0.66	0.70	0.84
b1	2.90	3.00	3.10
c	0.23	0.30	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
e1	4.60 BSC		
L	0.75	—	—
$\theta^\circ$	0	—	10

UNIT: MM

## Revision History

Revision	Date	Description
0.1	2009.12.23	Original

## Important Notice

All rights reserved.

No part of this document may be reproduced or duplicated in any form or by any means without the prior permission of ESMT.

The contents contained in this document are believed to be accurate at the time of publication. ESMT assumes no responsibility for any error in this document, and reserves the right to change the products or specification in this document without notice.

The information contained herein is presented only as a guide or examples for the application of our products. No responsibility is assumed by ESMT for any infringement of patents, copyrights, or other intellectual property rights of third parties which may result from its use. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of ESMT or others.

Any semiconductor devices may have inherently a certain rate of failure. To minimize risks associated with customer's application, adequate design and operating safeguards against injury, damage, or loss from such failure, should be provided by the customer when making application designs.

ESMT's products are not authorized for use in critical applications such as, but not limited to, life support devices or system, where failure or abnormal operation may directly affect human lives or cause physical injury or property damage. If products described here are to be used for such kinds of application, purchaser must do its own quality assurance testing appropriate to such applications.